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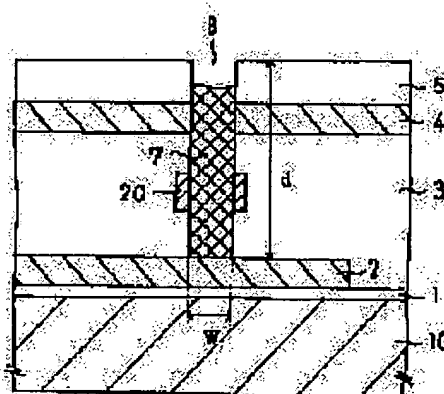
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## (54) SEMICONDUCTOR DEVICE AND ITS MANUFACTURE

(57)Abstract:

**PURPOSE:** To provide a structure for semiconductor device which is excellent in electric characteristics and can cope with an increase in degree of integration and a semiconductor device manufacturing method by which a semiconductor device having a multilayer interconnection structure can be manufactured through a simple manufacturing process.

**CONSTITUTION:** On a semiconductor substrate 10, an upper-layer wiring 4 is formed on a lower-layer wiring 2 with at least one layer insulating film 3 in between and an upper insulating film 5 is formed so as to coat the wiring 4. Then dummy wiring 20 is inserted between the upper- and lower-layer wiring. A contact hole 9 is formed against the upper- and lower-layer wiring including the dummy wiring from the top of the insulating film 5 and the hole 9 is filled with connecting wiring 7. The connecting wiring 7 surely provides electrical connection between the upper and lower-layer wiring.



## LEGAL STATUS

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